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# 3SK296

Silicon N-Channel Dual Gate MOS FET

# HITACHI

ADE-208-388  
1st. Edition

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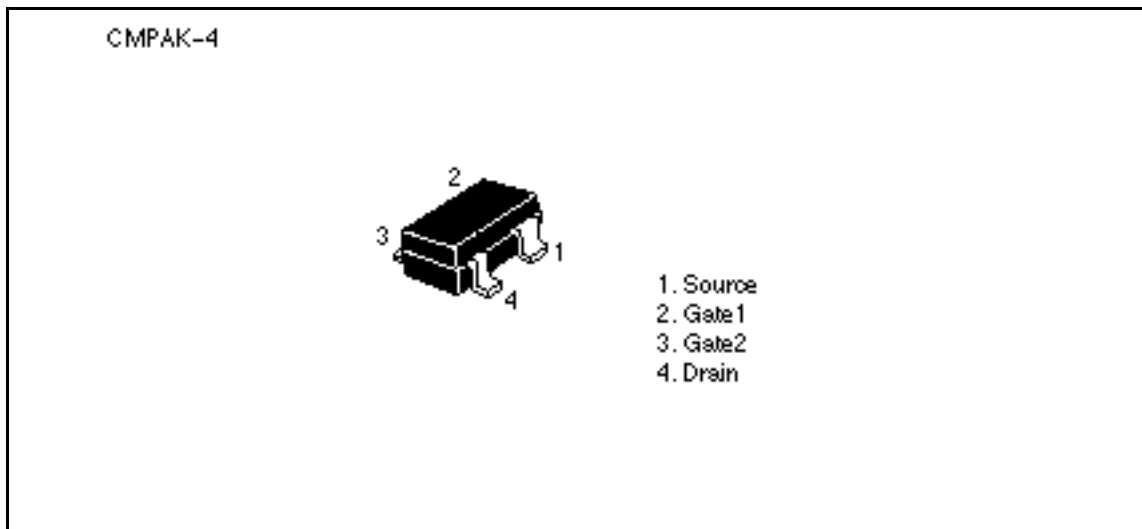
## Application

UHF RF amplifier

## Features

- Low noise figure.  
NF = 2.0 dB Typ. at f = 900 MHz
- Capable of low voltage operation

## Outline



## 3SK296

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DS}$	12	V
Gate 1 to source voltage	$V_{G1S}$	±8	V
Gate 2 to source voltage	$V_{G2S}$	±8	V
Drain current	$I_D$	25	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

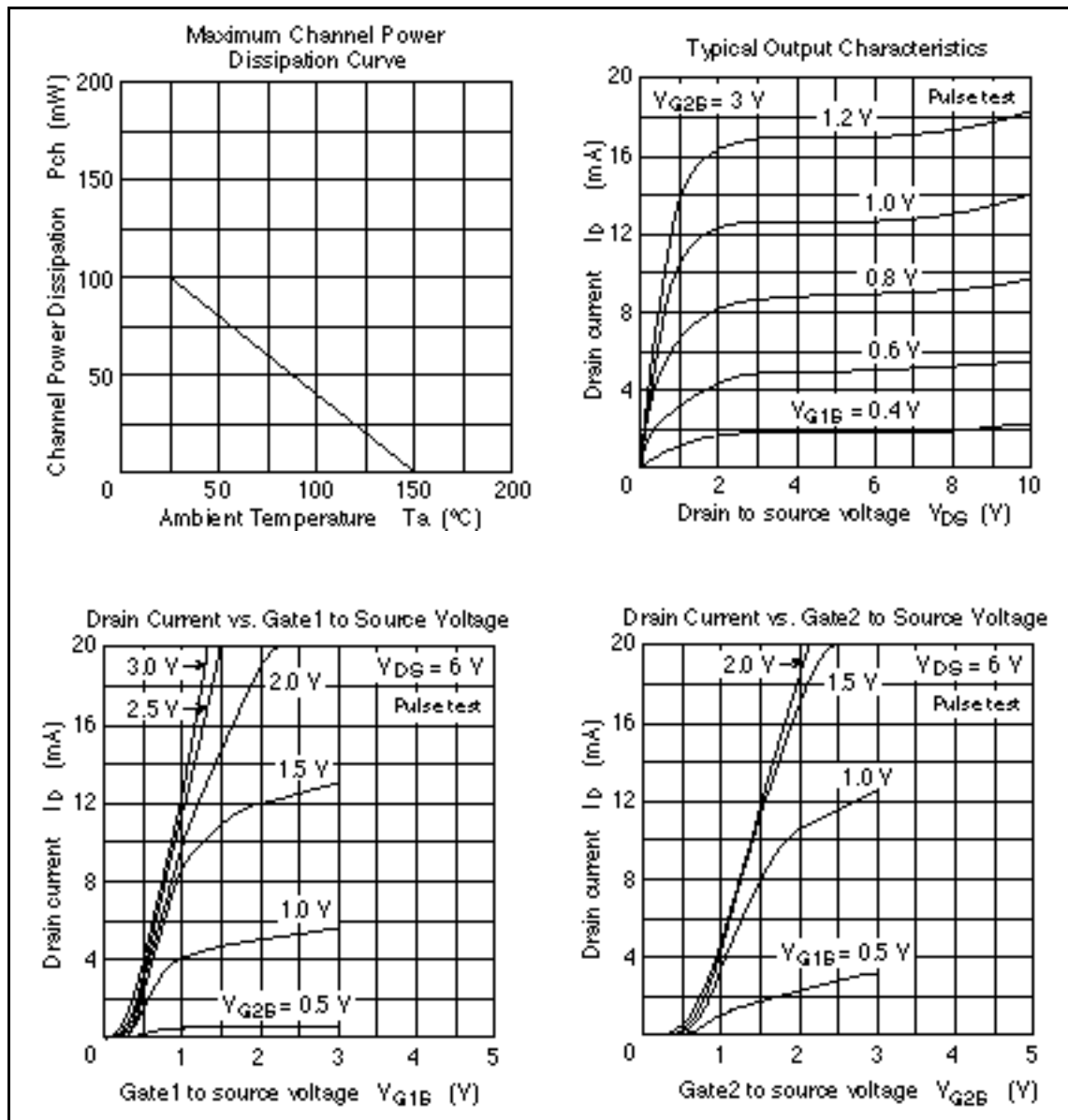
Attention: This device is very sensitive to electro static discharge.

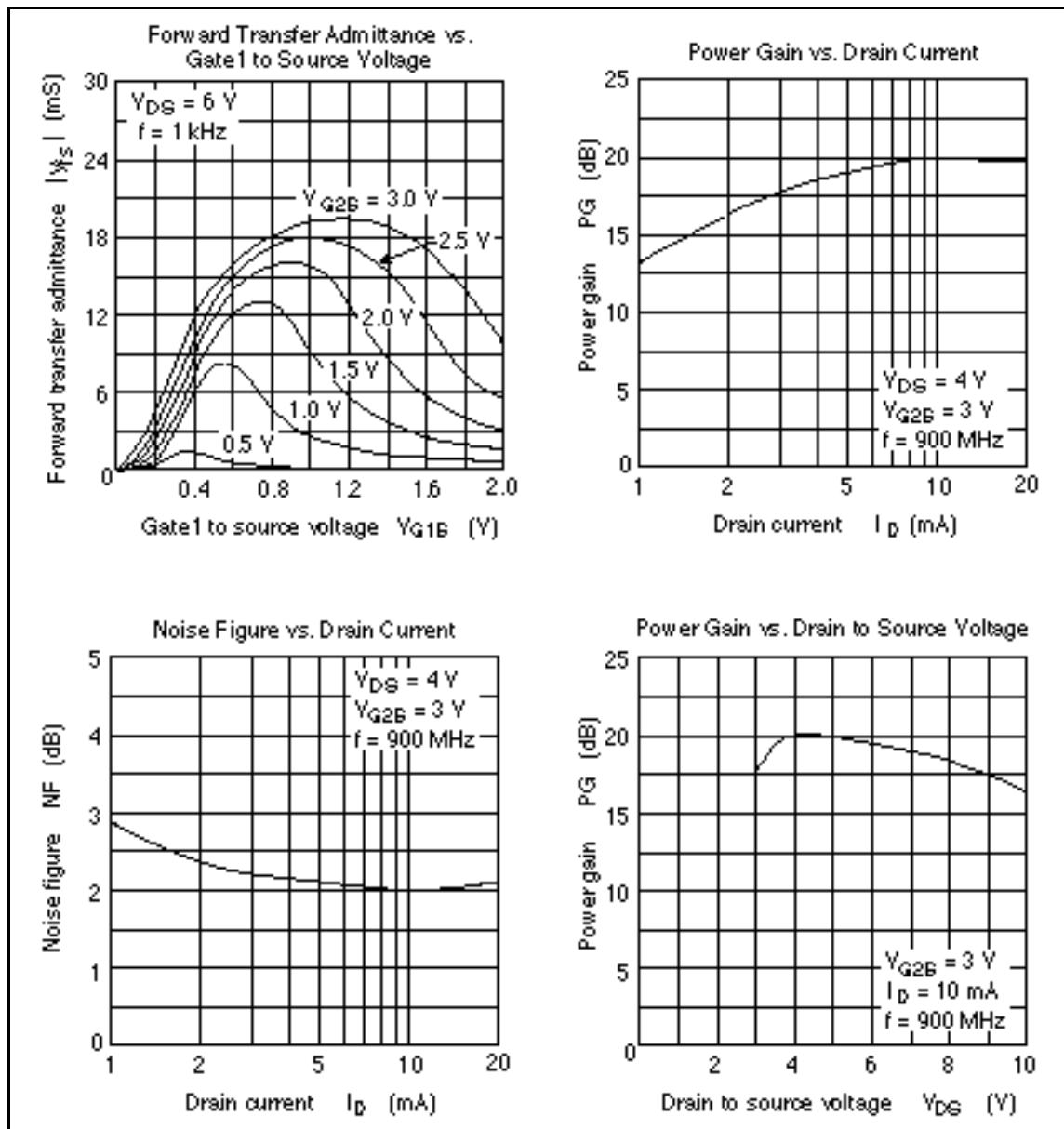
It is recommended to adopt appropriate cautions when handling this transistor.

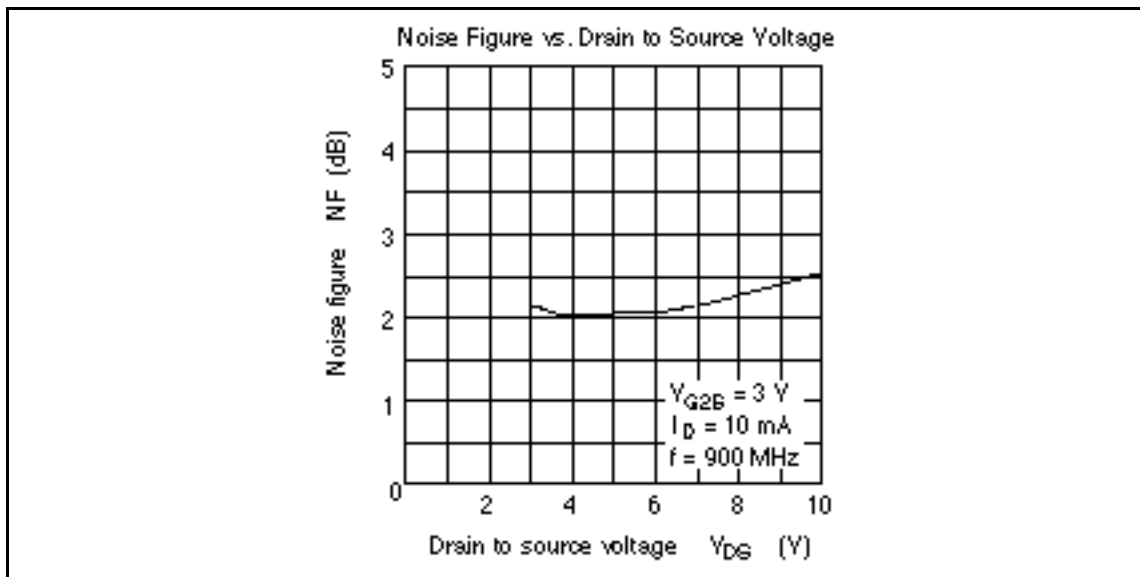
### Electrical Characteristics (Ta = 25°C)

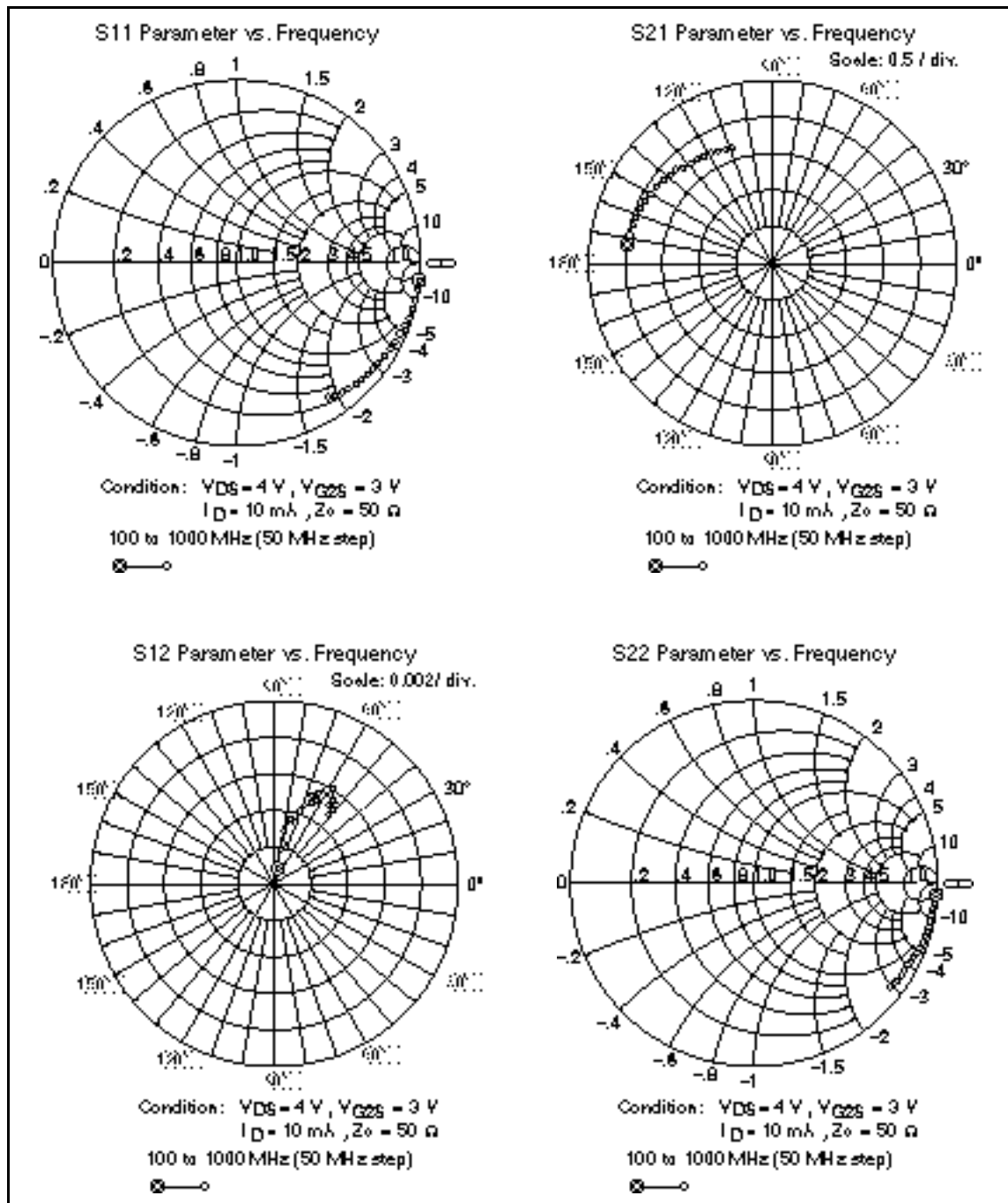
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	12	—	—	V	$I_D = 200 \mu A$ , $V_{G1S} = -3 V$ , $V_{G2S} = -3 V$
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	±8	—	—	V	$I_{G1} = \pm 10 \mu A$ , $V_{G2S} = V_{DS} = 0$
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	±8	—	—	V	$I_{G2} = \pm 10 \mu A$ , $V_{G1S} = V_{DS} = 0$
Gate 1 cutoff current	$I_{G1SS}$	—	—	±100	nA	$V_{G1S} = \pm 6 V$ , $V_{G2S} = V_{DS} = 0$
Gate 2 cutoff current	$I_{G2SS}$	—	—	±100	nA	$V_{G2S} = \pm 6 V$ , $V_{G1S} = V_{DS} = 0$
Drain current	$I_{DS(on)}$	0.5	—	10	mA	$V_{DS} = 6 V$ , $V_{G1S} = 0.5 V$ , $V_{G2S} = 3 V$
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	-0.5	—	+0.5	V	$V_{DS} = 10 V$ , $V_{G2S} = 3 V$ , $I_D = 100 \mu A$
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0	—	+1.0	V	$V_{DS} = 10 V$ , $V_{G1S} = 3 V$ , $I_D = 100 \mu A$
Forward transfer admittance	$ y_{fs} $	16	20.8	—	mS	$V_{DS} = 6 V$ , $V_{G2S} = 3 V$ , $I_D = 10 mA$ , $f = 1 kHz$
Input capacitance	Ciss	1.2	1.5	2.2	pF	$V_{DS} = 6 V$ , $V_{G2S} = 3 V$ , $I_D = 10 mA$ , $f = 1 MHz$
Output capacitance	Coss	0.6	0.9	1.2	pF	
Reverse transfer capacitance	Crss	—	0.01	0.03	pF	
Power gain	PG	16	19.5	—	dB	$V_{DS} = 4 V$ , $V_{G2S} = 3 V$ , $I_D = 10 mA$ , $f = 900 MHz$
Noise figure	NF	—	2.0	3	dB	

Note: Marking is "ZQ—"









**S Parameter** ( $V_{DS} = 4 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$ ,  $I_D = 10 \text{ mA}$ ,  $Z_0 = 50 \text{ } \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.999	-6.1	1.98	172.2	0.00094	79.2	0.989	-4.2
150	0.998	-9.1	1.97	168.4	0.00189	80.4	0.987	-6.1
200	0.992	-11.9	1.96	165.0	0.00230	79.5	0.986	-7.9
250	0.988	-14.8	1.96	161.0	0.00286	79.9	0.984	-9.8
300	0.985	-17.9	1.94	157.1	0.00364	75.2	0.981	-11.5
350	0.976	-20.6	1.92	153.7	0.00353	71.8	0.978	-13.4
400	0.971	-23.2	1.91	149.9	0.00419	70.7	0.975	-15.2
450	0.964	-26.3	1.88	146.8	0.00495	65.5	0.972	-17.2
500	0.961	-29.1	1.87	142.8	0.00509	62.7	0.968	-19.1
550	0.951	-32.2	1.86	139.4	0.00530	66.6	0.963	-20.8
600	0.949	-35.0	1.86	136.1	0.00550	63.8	0.960	-22.8
650	0.935	-37.6	1.81	132.9	0.00601	58.2	0.956	-24.5
700	0.933	-40.5	1.78	129.4	0.00582	60.6	0.950	-26.3
750	0.923	-42.9	1.77	125.7	0.00572	58.5	0.945	-28.0
800	0.916	-45.8	1.75	122.6	0.00553	56.3	0.941	-29.9
850	0.908	-49.0	1.72	119.1	0.00514	56.3	0.936	-31.7
900	0.900	-51.2	1.70	115.8	0.00543	52.9	0.930	-33.4
950	0.890	-54.0	1.67	112.6	0.00506	52.4	0.924	-35.2
1000	0.876	-56.4	1.65	109.3	0.00469	51.9	0.919	-37.0

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# HITACHI

## **Hitachi, Ltd.**

Semiconductor & IC Div.

Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

**Hitachi America, Ltd.**

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA 94005-4835

U.S.A.

Tel 415-589-8300

Fax 415-589-4207

**Hitachi Europe GmbH**

Electronic Components Group

Continental Europe

Darnecker Straße 3

D-85622 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

**Hitachi Europe Ltd.**

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

High Wycombe

Berkshire SL6 6YA

United Kingdom

Tel 0628-885000

Fax 0628-778322

**Hitachi Asia Pte. Ltd.**

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel 535-2100

Fax 535-1533

**Hitachi Asia (Hong Kong) Ltd.**

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074